

**Notice of References Cited**

Application/Control No.

09/530,588

Applicant(s)/Patent Under  
Reexamination  
MATSUSE ET AL.

Examiner

Tuan Quach

Art Unit

2814

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification	
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	B	US- -				
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	D	US- -				
	E	US- -				
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	G	US- -				
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	I	US- -				
	J	US- -				
	K	US- -				
	L	US- -				
	M	US- -				

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	O	JP-9-186102-A	07-1997	Japan	Hah et al.	H01L	21/28
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	Q	- -					
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**NON-PATENT DOCUMENTS**

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	U	Kasai et al., W/WNx/Poly-Si Gate . . . , IEEE IEDM Tech. Digest, December 1994, pp. 497-500.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.